Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection 1 kV
- Very low Drain-Source on-state resistance R<sub>DSon</sub> = 34 mΩ
- Very low threshold voltage of 0.65 V for portable applications

### 3. Applications

- Low-side load switch and charging switch for portable devices
- Power management in battery-driven portables
- LED driver
- DC-to-DC converters

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	12	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	3.2	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; $I_{D}$ = 3.2 A; $T_{j}$ = 25 °C		-	34	45	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D I
2	S	source	<u> </u>	
3	D	drain	4 3	G ( T)
4	D	drain	2	
			Transparent top view DFN1010D-3 (SOT1215)	S 017aaa255

# 6. Ordering information

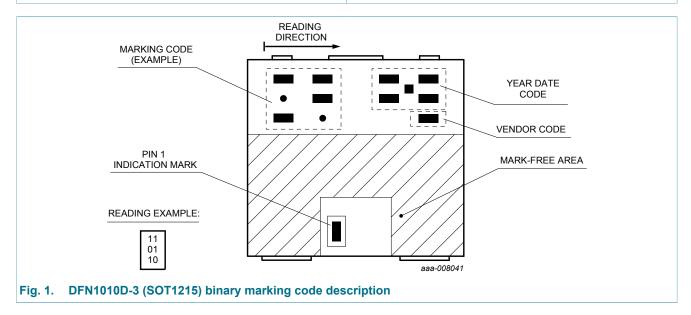
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMXB40UNE	DFN1010D-3	DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMXB40UNE	10 00 00



PMXB40UNE

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	12	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	$V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C	[1]	-	3.2	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	2.5	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	15	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	0.4	W
			[1]	-	1.07	W
		T <sub>sp</sub> = 25 °C		-	8.33	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	in diode		'	'		
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	1	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

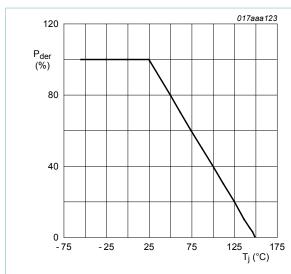


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

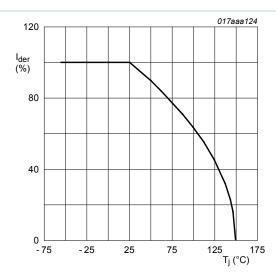


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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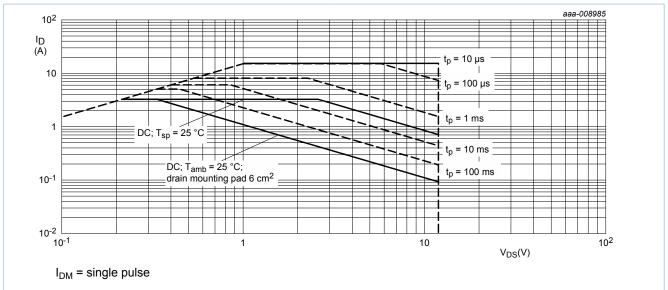


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	271	311	K/W
			[2]	-	102	117	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	10	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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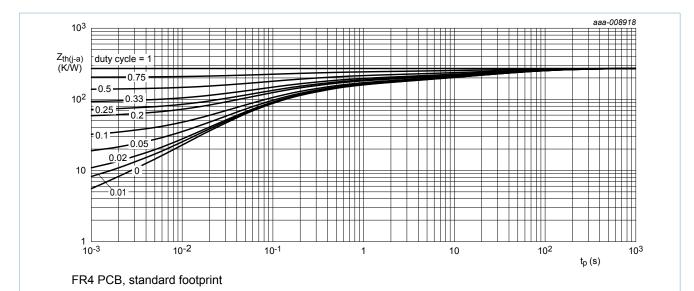
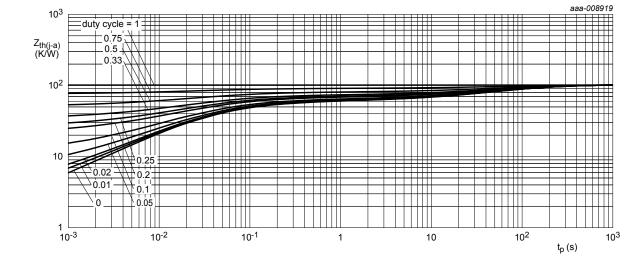


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain  $6~\mathrm{cm}^2$ 

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	12	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.2 A; T <sub>j</sub> = 25 °C	-	34	45	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.2 A; T <sub>j</sub> = 150 °C	-	49	67	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 3.2 A; T <sub>j</sub> = 25 °C	-	39	64	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 1 A; T <sub>j</sub> = 25 °C	-	46	85	mΩ
		V <sub>GS</sub> = 1.5 V; I <sub>D</sub> = 0.1 A; T <sub>j</sub> = 25 °C	-	50	100	mΩ
		V <sub>GS</sub> = 1.2 V; I <sub>D</sub> = 1 mA; T <sub>j</sub> = 25 °C	-	121	-	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_D$ = 2 A; $T_j$ = 25 °C	-	1.2	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic (	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 10 V; $I_{D}$ = 3.2 A; $V_{GS}$ = 4.5 V;	-	6.6	11.6	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.6	-	nC
$Q_{GD}$	gate-drain charge		-	1.7	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	556	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	107	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	94	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 3.2 A; V <sub>GS</sub> = 4.5 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	21	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	18	-	ns
t <sub>f</sub>	fall time		-	9	-	ns
Source-dr	rain diode		I	1	1	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 1 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.8	1.2	V

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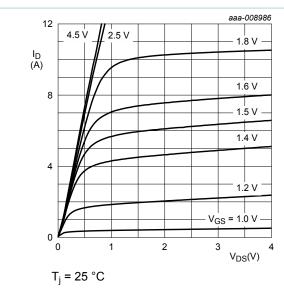


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

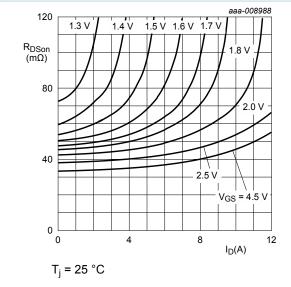


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

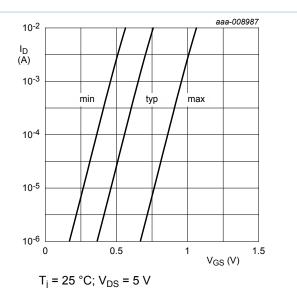


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

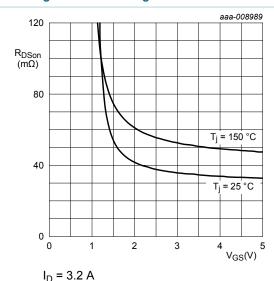


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 12 V, N-channel Trench MOSFET

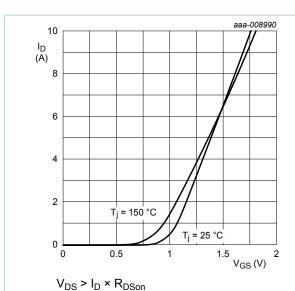


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

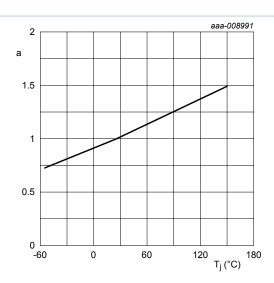


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

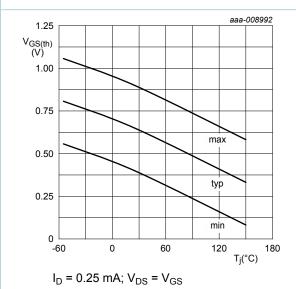


Fig. 13. Gate-source threshold voltage as a function of junction temperature

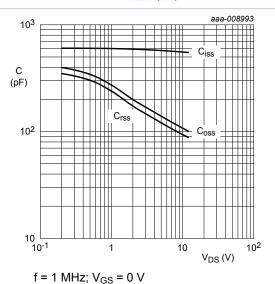


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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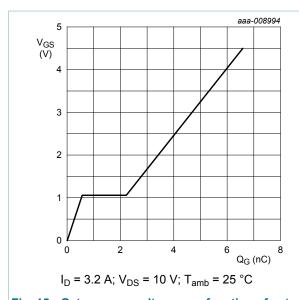


Fig. 15. Gate-source voltage as a function of gate charge; typical values

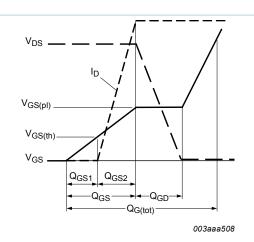


Fig. 16. MOSFET transistor: Gate charge waveform definitions

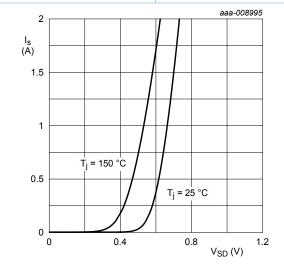
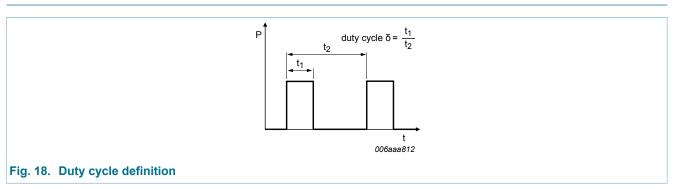


Fig. 17. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



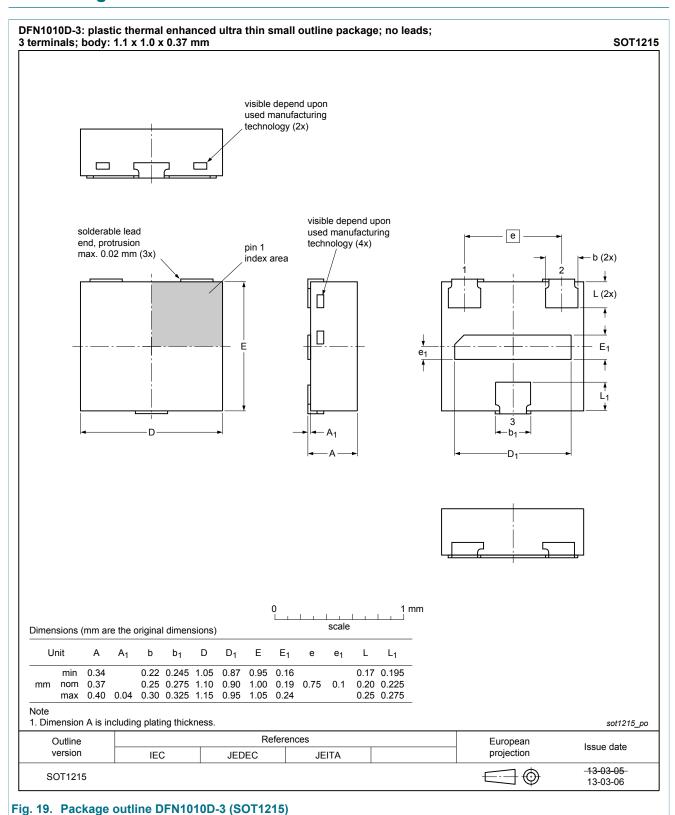
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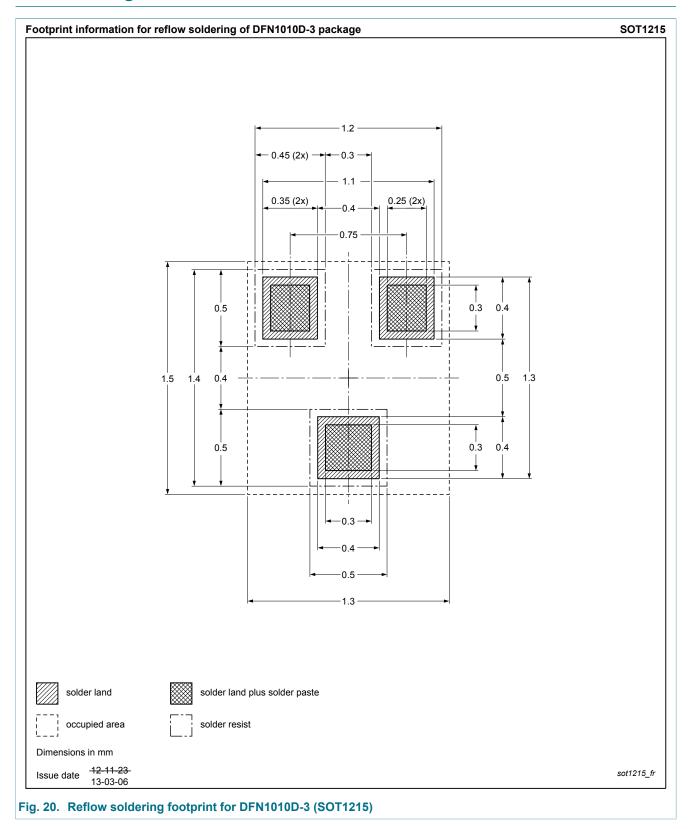
12 V, N-channel Trench MOSFET

# 12. Package outline



12 V, N-channel Trench MOSFET

# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMXB40UNE v.1	20130927	Product data sheet	-	-

#### 12 V, N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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